



AMENDMENTS TO THE CLAIMS

1. **(Currently Amended)** A polishing composition comprising polymer particles made of a thermoplastic resin or polymer particles made of a thermosetting resin, and inorganic particles in an aqueous medium, wherein the inorganic particles have an average particle size of from 20 to 130 nm, and wherein an average particle size D_p (nm) of said polymer particles and an average particle size D_i (nm) of said inorganic particles satisfy the following formula (1):

$$D_p \leq D_i + 50 \text{ nm} \quad (1)$$

wherein the inorganic particles are colloidal silica, and further wherein the pH of the polishing composition is from 10.5-12, ~~7-12~~.

2. **(Original)** The polishing composition according to claim 1, wherein the polymer particles are made of a thermoplastic resin.

3. **(Original)** The polishing composition according to claim 1, wherein the polymer particles are made of a resin having a glass transition temperature of 200°C or less.

4. **(Original)** The polishing composition according to claim 1, wherein the polymer particles are made of a resin having a degree of cross-linking of 50 or less.

5. **(Previously Presented)** The polishing composition according to claim 1, wherein the polymer particles and the inorganic particles have a zeta potential of zero or the same sign.

6. **(Original)** The polishing composition according to claim 1, wherein a ratio of C_p/C_i is from 0.03 to 2, wherein C_p is a content of the polymer particles in the polishing composition and C_i is a content of the inorganic particles in the polishing composition.

7. **(Currently Amended)** A polishing process for a substrate to be polished comprising polishing the substrate to be polished with the polishing composition as defined in any one of claims 1 to 6, wherein the substrate is a silicon substrate, a polysilicon polysilicene substrate, ~~or a silicon oxide film, an aluminum alloy substrate plated with Ni-P, or comprises~~ silicon dioxide.

8. **(Previously Presented)** A process for improving a rate for polishing a substrate to be polished using the polishing composition as defined in any one of claims 1 to 6.

9. **(Previously Presented)** The polishing process according to claim 7, wherein the substrate to be polished is a substrate having silicon dioxide.

10. **(Previously Presented)** The polishing process according to claim 7, wherein the substrate to be polished is an aluminum alloy substrate plated with Ni-P.

11– 13. **(Canceled)**